

Title of Change:	FAN8811TMPX Voltage spike immunity and Breakdown Voltage spec update		
Proposed first ship date:	2 May 2018 or earlier upon customer approval		
Contact information:	Contact your local ON Semiconductor Sales Office or <scott.brow@onsemi.com></scott.brow@onsemi.com>		
Samples:	Contact your local ON Semiconductor Sales Office		
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office		
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>		
Change Part Identification:	Product shipped after WW17 2018 will be built with die with the design modification listed in this notification.		
Change category:	Wafer Fab Change Assembly Change Test Change Other Design Change		
Change Sub-Category(s): Manufacturing Site Change Manufacturing Process Cha	[Multiple options might be applicable] Image Datasheet/Product Doc change /Addition Image Material Change Image nge Image Shipping/Packaging/Marking Image Image Other: Image Image Image Image		
Sites Affected:	ON Semiconductor Sites:External Foundry/Subcon Sites:ON S. Portland, MaineUTAC		
Description and Purpose:			

This notification is to inform customers of (2) changes to the FAN8811TMPX. During additional temperature characterization, it was found that the product is not capable of meeting the current 120V Breakdown voltage over temperature as specified in the datasheet. Based on the results, the datasheet will be modified to show a maximum breakdown of 100V as shown here:

Symbol	Sumbol		Old	New	Linite
Symbol	Parameter	IVIIII	Max	Max	Units
VUC	High-Side Floating Supply Offset Voltage(Note 2)	-1	118	100	V
VHS	Repetitive Pulse (< 100 ns)(Note 3)	-(24 – VDD)	118	100	V

Additionally, some customer interactions showed that the product had a lower High Voltage spike immunity than competitor products. In order to improve the device performance an additional SCR ESD Diode in the Half-bridge structure of the device has been added. By adding this structure, the product is now able to handle a significantly higher voltage spike than before.



Reliability	y Data	Summary	y :
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There is no reliability data associated with this notification. Only ESD validation and electrical characterization is necessary.

Electrical	Characteristic	Summary:
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Voltage Spike Immunity:

	DC-BV	Voltage spike immunity
Competitor	127V	145V
FAN8811	131V	128V
Revised FAN8811	almostsame	Around 150V

ESD Results:

	Current FAN8811	Revised FAN8811
HBM	>2kV	>2kV
CDM	>1kV	>1kV

List of Affected Standard Parts:

Part Number	Qualification Vehicle
FAN8811TMPX	FAN8811TMPX